

**INFORMATION DISCLOSURE
CITATION IN AN
APPLICATION**
(PTO-1449)

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APPLICANT
Kenji WATANABE et al

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1792

U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE

FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						Yes	No

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

/G.N.R./	Shojiro Komatsu, September 24, 2002; Vol 63, No. 1, Page 116 (26p-D-3), PLD PURAZUMAASHISUTEDO modulation method (MPA-PLD) from sp3-bonded 5H-BN of 225nm ultraviolet light emitting
/G.N.R./	A new Flux for Growing Hexagonal Boron Nitride Crystals at Low Temperature, page L300 to L302, Masaichi yano et al; February 14, 2000
/G.N.R./	Growth of Single Crystals of Hexagonal Boron Nitride; Journal of Crystal Growth 61 (1983) 689 to 690; North-Holland Publishing company; T. Ishii and T. Sato
EXAMINER /G. Nagesh Rao/ (05/26/2009)	DATE CONSIDERED 05/26/2009

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